

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2SA1803

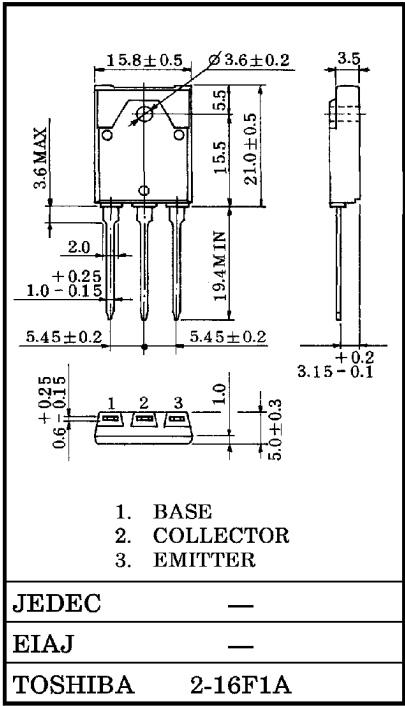
POWER AMPLIFIER APPLICATIONS

Unit in mm

- Complementary to 2SC4688
- Recommend for 40W High Fidelity Audio Frequency Amplifier output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V _{CBO}	−80	V
Collector-Emitter Voltage		V _{CEO}	−80	V
Emitter-Base Voltage		V _{EBO}	−5	V
Collector Current	DC	I _C	−6	A
	Pulse	I _{CP}	−12	
Base Current		I _B	−0.6	A
Collector Power Dissipation (Tc = 25°C)		P _C	55	W
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	−55~150	°C



Weight : 5.8g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = −80V, I _E = 0	—	—	−5.0	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = −5V, I _C = 0	—	—	−5.0	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = −50mA, I _B = 0	−80	—	—	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} = −5V, I _C = −1A	55	—	160	
	h _{FE} (2)	V _{CE} = −5V, I _C = −3A	35	80	—	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = −5A, I _B = −0.5A	—	−1.0	−2.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = −5V, I _C = −3A	—	−0.95	−1.5	V
Transition Frequency	f _T	V _{CE} = −5V, I _C = −1A	—	30	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = −10V, I _E = 0, f = 1MHz	—	290	—	pF

Note : h_{FE}(1) Classification R : 55~110, O : 80~160

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